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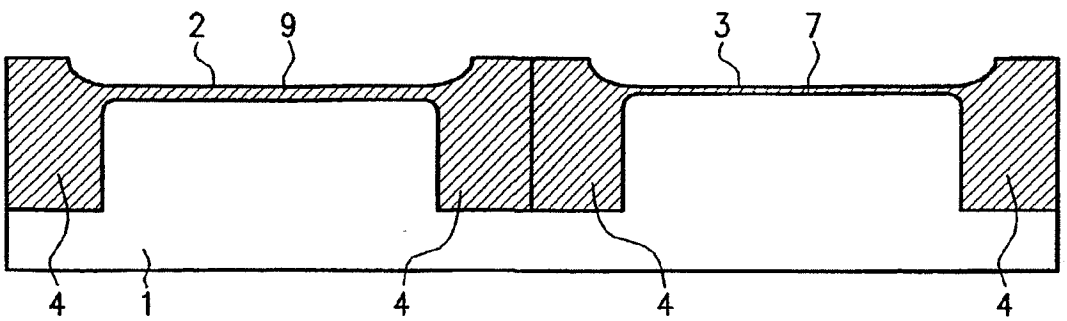
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(54) Title: METHOD OF FORMING LAYERS OF OXIDE OF DIFFERENT THICKNESSES ON A SURFACE OF A SUBSTRATE



(57) Abstract: A method of forming oxide layers of different thickness on a substrate (1) is disclosed, wherein the oxide layers preferably serve as gate insulation layers of field effect transistors. The method allows to form very thin, high quality oxide layers with a reduced number of masking steps compared to the conventional processing, wherein the thickness difference can be maintained within a range of some tenths of a nanometer. The method substantially eliminates any high temperature oxidations and is also compatible with most chemical vapor deposition techniques used for gate dielectric deposition in sophisticated semiconductor devices

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